

Mercury Cadmium Telluride Semiconductors Semimetals Vol 18

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New Ternary Alloy Systems for Infrared Detectors Antoni Rogalski 1994

Silicon-Germanium Strained Layers and Heterostructures M. Willander 2003-10-02 The study of Silicone Germanium strained layers has broad implications for material scientists and engineers, in particular those working on the design and modelling of semi-conductor devices. Since the publication of the original volume in 1994, there has been a steady flow of new ideas, new understanding, new Silicon-Germanium (SiGe) structures and new devices with enhanced performance. Written for both students and senior researchers, the 2nd edition of Silicon-Germanium Strained Layers and Heterostructures provides an essential up-date of this important topic, describing in particular the recent developments in technology and modelling. * Fully-revised and updated 2nd edition incorporating important recent breakthroughs and a complete literature review * The extensive bibliography of over 400 papers provides a comprehensive and coherent overview of the subject * Appropriate for students and senior researchers

Handbook of Laser Technology and Applications: Laser design and Laser systems Colin E. Webb 2004

High Pressure Semiconductor Physics I 1998-09-09 Since its inception in 1966, the series of numbered volumes known as Semiconductors and Semimetals has distinguished itself through the careful selection of well-known authors, editors, and contributors. The "Willardson and Beer" Series, as it is widely known, has succeeded in publishing numerous landmark volumes and chapters. Not only did many of these volumes make an impact at the time of their publication, but they continue to be well-cited years after their original release. Recently, Professor Eicke R. Weber of the University of California at Berkeley joined as a co-editor of the series. Professor Weber, a well-known expert in the field of semiconductor materials, will further contribute to continuing the series' tradition of publishing timely, highly relevant, and long-impacting volumes. Some of the recent volumes, such as Hydrogen in Semiconductors, Imperfections in III/V Materials, Epitaxial Microstructures, High-Speed Heterostructure Devices, Oxygen in Silicon, and others promise indeed that this tradition will be maintained and even expanded. Reflecting the truly interdisciplinary nature of the field that the series covers, the volumes in Semiconductors and Semimetals have been and will continue to be of great interest to physicists, chemists, materials scientists, and device engineers in modern industry. Volumes 54 and 55 present contributions by leading researchers in the field of high pressure semiconductors. Edited by T. Suski and W. Paul, these volumes continue the tradition of well-known but outdated publications such as Brigman's The Physics of High Pressure (1931 and 1949) and High Pressure Physics and Chemistry edited by Bradley. Volumes 54 and 55 reflect the industrially important recent developments in research and applications of semiconductor properties and behavior under desirable risk-free conditions at high pressures. These developments include the advent of the diamond anvil cell technique and the availability of commercial piston cylinder apparatus operating at high hydrostatic pressures. These much-needed books will be useful to both researchers and practitioners in applied physics, materials science, and engineering.

Nonlinear Optics in Semiconductors I 1998-10-22 Since its inception in 1966, the series of numbered volumes known as Semiconductors and Semimetals has distinguished itself through the careful selection of well-known authors, editors, and contributors. The "Willardson and Beer" Series, as it is widely known, has succeeded in publishing numerous landmark volumes and chapters. Not only did many of these volumes make an impact at the time of their publication, but they continue to be well-cited years after their original release. Recently, Professor Eicke R. Weber of the University of California at Berkeley joined as a co-editor of the series. Professor Weber, a well-known expert in the field of semiconductor materials, will further contribute to continuing the series' tradition of publishing timely, highly relevant, and long-impacting volumes. Some of the recent volumes, such as Hydrogen in Semiconductors, Imperfections in III/V Materials, Epitaxial Microstructures, High-Speed Heterostructure Devices, Oxygen in Silicon, and others promise that this tradition will be maintained and even expanded. Reflecting the truly interdisciplinary nature of the field that the series covers, the volumes in Semiconductors and Semimetals have been and will continue to be of great interest to physicists, chemists, materials scientists, and device engineers in modern industry.

Handbook of Laser Technology and Applications (Three- Volume Set) Colin Webb 2003-12-01 The invention of the laser was one of the towering achievements of the twentieth century. At the opening of the twenty-first century we are witnessing the burgeoning of the myriad technical innovations to which that invention has led. The Handbook of Laser Technology and Applications is a practical and long-lasting reference source for scientists a

Optical Absorption of Impurities and Defects in Semiconducting Crystals Bernard Pajot 2010-05-26 Semiconducting and Insulating Crystals details how absorption spectroscopy provides information on the nature, concentration, charge state and configuration of impurities in crystals and also on their kinetics and transformations under annealing. After an introduction of the bulk optical properties of semiconductors and insulators and of impurities in crystals, this book presents the physical bases necessary for the understanding of impurity spectra. The description of various set-ups and accessories used in absorption spectroscopy is followed by a presentation of experimental results on specific impurities and classes of impurities and their relation with those obtained by various computation and by other experimental techniques.

The GEC Journal of Research 1988

Long Wavelength Infrared Emitters Based on Quantum Wells and Superlattices Manfred Helm 2000-10-31 This book offers a thorough survey of long wavelength infrared semiconductor emitters based primarily on quantum wells and superlattices. Featuring contributions from the most prominent researchers in the field, this volume allows readers to compare different types of lasers as well as examine investigations of potential far-infrared/terahertz sources. This is an essential reference for researchers, engineers and graduate students who wish to obtain comprehensive knowledge about infrared semiconductor sources and recent developments in this field.

Infrared Photon Detectors Antoni Rogalski 1995

Narrow-gap Semiconductor Photodiodes Antoni Rogalski 2000 In this monograph, investigations of the performance of narrow-gap semiconductor photodiodes are presented, and recent progress in different IR photodiode technologies is discussed: HgCdTe photodiodes, InSb photodiodes, alternatives to HgCdTe III-V and

II-VI ternary alloy photodiodes, lead chalcogenide photodiodes, and a new class of photodiodes based on two-dimensional solids. Investigations of the performance of photodiodes operated in different spectral regions are presented.

Infrared Detectors and Emitters: Materials and Devices Peter Capper 2013-11-27 An up-to-date view of the various detector/emitter materials systems currently in use or being actively researched. The book is aimed at newcomers and those already working in the IR industry. It provides both an introductory text and a valuable overview of the entire field.

Recent Trends in Thermoelectric Materials Research 2001

Thin-Film Diamond II Christopher Nebel 2004-04-19 Part II reviews the state of the art of thin film diamond a very promising new semiconductor that may one day rival silicon as the material of choice for electronics. Diamond has the following important characteristics; it is resistant to radiation damage, chemically inert and biocompatible and it will become "the material" for bio-electronics, in-vivo applications, radiation detectors and high-frequency devices. Thin-Film Diamond II is the first book to summarize state of the art of CVD diamond in depth. It covers the most recent results regarding growth and structural properties, doping and defect characterization, hydrogen in and on diamond as well as surface properties in general, applications of diamond in electrochemistry, as detectors, and in surface acoustic wave devices * Accessible by both experts and non-experts in the field of semi-conductors research and technology, each chapter is written in a tutorial format * Assisting engineers to manufacture devices with optimized electronic properties * Truly international, this volume contains chapters written by recognized experts representing academic and industrial institutions from Europe, Japan and the US

Physics and Properties of Narrow Gap Semiconductors Junhao Chu 2007-11-21 Narrow gap semiconductors are the most important materials for the preparation of advanced modern infrared systems. They often operate at the extremes of the rules of semiconductor science. This book offers clear descriptions of crystal growth and the fundamental structure and properties of these unique materials. Topics covered include band structure, optical and transport properties, and lattice vibrations and spectra. A thorough treatment of the properties of low-dimensional systems and their relation to infrared applications is provided.

Comprehensive Semiconductor Science and Technology 2011-01-28 Semiconductors are at the heart of modern living. Almost everything we do, be it work, travel, communication, or entertainment, all depend on some feature of semiconductor technology. Comprehensive Semiconductor Science and Technology captures the breadth of this important field, and presents it in a single source to the large audience who study, make, and exploit semiconductors. Previous attempts at this achievement have been abbreviated, and have omitted important topics. Written and Edited by a truly international team of experts, this work delivers an objective yet cohesive global review of the semiconductor world. The work is divided into three sections. The first section is concerned with the fundamental physics of semiconductors, showing how the electronic features and the lattice dynamics change drastically when systems vary from bulk to a low-dimensional structure and further to a nanometer size. Throughout this section there is an emphasis on the full understanding of the underlying physics. The second section deals largely with the transformation of the conceptual framework of solid state physics into devices and systems which require the growth of extremely high purity, nearly defect-free bulk and epitaxial materials. The last section is devoted to exploitation of the knowledge described in the previous sections to highlight the spectrum of devices we see all around us. Provides a comprehensive global picture of the semiconductor world Each of the work's three sections presents a complete description of one aspect of the whole Written and Edited by a truly international team of experts

Molecular Beam Epitaxy John Wilfred Orton 2015 The book is a history of Molecular Beam Epitaxy (MBE) as applied to the growth of semiconductor thin films (note that it does not cover the subject of metal thin films). It begins by examining the origins of MBE, first of all looking at the nature of molecular beams and considering their application to fundamental physics, to the development of nuclear magnetic resonance and to the invention of the microwave MASER. It shows how molecular beams of silane (SiH₄) were used to study the nucleation of silicon films on a silicon substrate and how such studies were extended to compound semiconductors such as GaAs. From such surface studies in ultra-high vacuum the technique developed into a method of growing high quality single crystal films of a wide range of semiconductors. Comparing this with earlier evaporation methods of deposition and with other epitaxial deposition methods such as liquid phase and vapour phase epitaxy (LPE and VPE). The text describes the development of MBE machines from the early 'home-made' variety to that of commercial equipment and show how MBE was gradually refined to produce high quality films with atomic dimensions. This was much aided by the use of various in-situ surface analysis techniques, such as reflection high energy electron diffraction (RHEED) and mass spectrometry, a feature unique to MBE. It looks at various modified versions of the basic MBE process, then proceed to describe their application to the growth of so-called 'low-dimensional structures' (LDS) based on ultra-thin heterostructure films with thickness of order a few molecular monolayers. Further chapters cover the growth of a wide range of different compounds and describe their application to fundamental physics and to the fabrication of electronic and opto-electronic devices. The authors study the historical development of all these aspects and emphasise both the (often unexpected) manner of their discovery and development and the unique features which MBE brings to the growth of extremely complex structures with monolayer accuracy.

Mid-infrared Optoelectronics Eric Tournié 2019-10-19 Mid-infrared Optoelectronics: Materials, Devices, and Applications addresses the new materials, devices and applications that have emerged over the last decade, along with exciting areas of research. Sections cover fundamentals, light sources, photodetectors, new approaches, and the application of mid-IR devices, with sections discussing LEDs, laser diodes, and quantum cascade lasers, mid-infrared optoelectronics, emerging research areas, dilute bismide and nitride alloys, Group-IV materials, gallium nitride heterostructures, and new nonlinear materials. Finally, the most relevant applications of mid-infrared devices are reviewed in industry, gas sensing, spectroscopy, and imaging. This book presents a key reference for materials scientists, engineers and professionals working in R&D in the area of semiconductors and optoelectronics. Provides a comprehensive overview of mid-infrared photodetectors and light sources and the latest materials and devices Reviews emerging areas of research in the field of mid-infrared optoelectronics,

including new materials, such as wide bandgap materials, chalcogenides and new approaches, like heterogeneous integration. Includes information on the most relevant applications in industry, like gas sensing, spectroscopy and imaging.

Physics of Semiconductor Devices K. N. Bhat 2004 Contributed papers of the workshop held at IIT, Madras, in 2003.

Handbook of Laser Technology and Applications Colin Webb 2020-09-30 The invention of the laser was one of the towering achievements of the twentieth century. At the opening of the twenty-first century we are witnessing the burgeoning of the myriad technical innovations to which that invention has led. The Handbook of Laser Technology and Applications is a practical and long-lasting reference source for scientists and engineers who work with lasers. The Handbook provides, a comprehensive guide to the current status of lasers and laser systems; it is accessible to science or engineering graduates needing no more than standard undergraduate knowledge of optics. Whilst being a self-contained reference work, the Handbook provides extensive references to contemporary work, and is a basis for studying the professional journal literature on the subject. It covers applications through detailed case studies, and is therefore well suited to readers who wish to use it to solve specific problems of their own. The first of the three volumes comprises an introduction to the basic scientific principles of lasers, laser beams and non-linear optics. The second volume describes the mechanisms and operating characteristics of specific types of laser including crystalline solid - state lasers, semiconductor diode lasers, fibre lasers, gas lasers, chemical lasers, dye lasers and many others as well as detailing the optical and electronic components which tailor the laser's performance and beam delivery systems. The third volume is devoted to case studies of applications in a wide range of subjects including materials processing, optical measurement techniques, medicine, telecommunications, data storage, spectroscopy, earth sciences and astronomy, and plasma fusion research. This vast compendium of knowledge on laser science and technology is the work of over 130 international experts, many of whom are recognised as the world leaders in their respective fields. Whether the reader is engaged in the science, technology, industrial or medical applications of lasers or is researching the subject as a manager or investor in technical enterprises they cannot fail to be informed and enlightened by the wide range of information the Handbook supplies.

Quantum Well Intersubband Transition Physics and Devices Hui C. Liu 2012-12-06 Intersubband transitions in quantum wells have attracted tremendous attention in recent years, mainly due to the promise of applications in the mid and far-infrared regions (2--20 μm). Many of the papers presented in Quantum Well Intersubband Transition Physics and Devices are on the basic linear intersubband transition processes, detector physics and detector application, reflecting the current state of understanding and detector applications, where highly uniform, large focal plane arrays have been demonstrated. Other areas are still in their early stages, including infrared modulation, harmonic generation and emission.

Infrared and Terahertz Detectors, Third Edition Antoni Rogalski 2019-01-10 This new edition of Infrared and Terahertz Detectors provides a comprehensive overview of infrared and terahertz detector technology, from fundamental science to materials and fabrication techniques. It contains a complete overhaul of the contents including several new chapters and a new section on terahertz detectors and systems. It includes a new tutorial introduction to technical aspects that are fundamental for basic understanding. The other dedicated sections focus on thermal detectors, photon detectors, and focal plane arrays.

Infrared Detectors Antonio Rogalski 2010-11-15 Completely revised and reorganized while retaining the approachable style of the first edition, Infrared Detectors, Second Edition addresses the latest developments in the science and technology of infrared (IR) detection. Antoni Rogalski, an internationally recognized pioneer in the field, covers the comprehensive range of subjects necessary to an

Mercury Cadmium Telluride Imagers A.C. Onshage 1997-06-18 In two parts, this book describes the evolution of mercury cadmium telluride (HgCdTe) imager structures based upon published patents and patent applications. The first part covers monolithic arrays, and the second part describes hybrid arrays. Each part has 5 chapters, with each document placed in chronological order, with the documents with the earliest priority placed first. Focus has been directed at the steps of manufacturing and structures of imagers. There is an index at the end of the book containing the patent number, the name of the applicant and the date of publication of each cited document. This monograph will serve as a useful summary of the patents and patent applications in the field of mercury cadmium telluride imagers.

Physics of Photonic Devices Shun Lien Chuang 2012-11-07 The most up-to-date book available on the physics of photonic devices. This new edition of Physics of Photonic Devices incorporates significant advancements in the field of photonics that have occurred since publication of the first edition (Physics of Optoelectronic Devices). New topics covered include a brief history of the invention of semiconductor lasers, the Lorentz dipole method and metal plasmas, matrix optics, surface plasma waveguides, optical ring resonators, integrated electroabsorption modulator-lasers, and solar cells. It also introduces exciting new fields of research such as: surface plasmonics and micro-ring resonators; the theory of optical gain and absorption in quantum dots and quantum wires and their applications in semiconductor lasers; and novel microcavity and photonic crystal lasers, quantum-cascade lasers, and GaN blue-green lasers within the context of advanced semiconductor lasers. Physics of Photonic Devices, Second Edition presents novel information that is not yet available in book form elsewhere. Many problem sets have been updated, the answers to which are available in an all-new Solutions Manual for instructors. Comprehensive, timely, and practical, Physics of Photonic Devices is an invaluable textbook for advanced undergraduate and graduate courses in photonics and an indispensable tool for researchers working in this rapidly growing field.

Handbook of Luminescent Semiconductor Materials Leah Bergman 2016-04-19 Photoluminescence spectroscopy is an important approach for examining the optical interactions in semiconductors and optical devices with the goal of gaining insight into material properties. With contributions from researchers at the forefront of this field, Handbook of Luminescent Semiconductor Materials explores the use of this technique to study semiconductor materials in a variety of applications, including solid-state lighting, solar energy conversion, optical devices, and biological imaging. After introducing basic semiconductor theory and photoluminescence principles, the book focuses on the optical properties of wide-bandgap semiconductors, such as AlN, GaN, and ZnO. It then presents research on narrow-bandgap semiconductors and solid-state lighting. The book also covers the optical properties of semiconductors in the nanoscale regime, including quantum dots and nanocrystals. This handbook explains how photoluminescence spectroscopy is a powerful and practical analytical tool for revealing the fundamentals of light interaction and, thus, the optical properties of semiconductors. The book shows how luminescent semiconductors are used in lasers, photodiodes, infrared detectors, light-emitting diodes, solid-state lamps, solar energy, and biological imaging.

Handbook of Infrared Detection Technologies M. Henini 2002-12-11 The use of lasers which emit infra-red radiation and sophisticated detectors of IR radiation is increasing dramatically; they are being used for long-distance fibre-optic communications and remote environmental monitoring and sensing. Thus they are of interest to the telecommunications industry and the military in particular. This

book has been designed to bring together what is known on these devices, using an international group of contributors.

II-VI Semiconductor Compounds Mukesh Jain 1993-05-04 Contents: X-Ray Characterisation of II-VI Semiconductor Materials (D Gao et al.) Electronic Structure of II-VI Semiconductors and Their Alloys (S-H Wei) Radiative Recombination Processes in Rare Earth Doped II-VI Materials (M Godlewski et al.) Nonlinear Optical Properties of Heavily Doped CdS (U Neukirch) Nanostructures of Broad Gap (II,Mn) VI Semiconductors (W Heimbrodt & O Goede) Co-Based II-VI Semimagnetic Semiconductors (A Twardowski et al.) Photoluminescence and Raman Scattering of ZnSe-ZnTe Strained Layer Superlattices (K Kumazaki) Novel Electronic Processes in Mercury-Based Superlattices (J R Meyer et al.) Strain, Pressure and Piezoelectric Effects in Strained II-VI Superlattices and Heterostructures (E Anastassakia) Electronic Structures of Strained II-VI Superlattices (T Nakayama) Devices and Applications of II-VI Compounds (S Colak) Solar Cells Based on II-VI Semiconductors (H Uda) ZnSe and Its Applications for Blue-Light Laser Diodes (M Pessa & D Ahn) Molecular Beam Epitaxy of HgCdTe for Electro-Optical Infrared Applications (J M A Cortés) and other papers. Readership: Condensed matter physicists and electronic engineers. keywords:

Semiconductors and Semimetals 1982-03-18 Semiconductors and Semimetals

Development of 15 Micron Cutoff Wavelength HgCdTe Detector Arrays for Astronomy Mario Cabrera 2020-09-17 This thesis describes advances in the understanding of HgCdTe detectors. While long wave (15 μm) infrared detectors HgCdTe detectors have been developed for military use under high background irradiance, these arrays had not previously been developed for astronomical use where the background irradiance is a billion times smaller. The main pitfall in developing such arrays for astronomy is the pixel dark current which plagues long wave HgCdTe. The author details work on the success of shorter wavelength development at Teledyne Imaging Sensors, carefully modeling the dark current-reverse bias voltage curves of their 10 μm devices at a temperature of 30K, as well as the dark current-temperature curves at several reverse biases, including 250 mV. By projecting first to 13 and then 15 μm HgCdTe growth, values of fundamental properties of the material that would minimize tunneling dark currents were determined through careful modeling of the dark current-reverse bias voltage curves, as well as the dark current-temperature curves. This analysis was borne out in the 13 μm parts produced by Teledyne, and then further honed to produce the necessary parameters for the 15 μm growth. The resulting 13 μm arrays are being considered by a number of ground-based astronomy research groups.

Mercury Handbook L F Kozin 2013-10-15 Mercury has many applications in scientific research and industry from amalgams for dental restoration to light bulbs. Developed from a combination of material originally published in Russian and the authors' research knowledge, this book provides a comprehensive treatise on the chemistry and metallurgy of amalgams. Coverage includes analysis, physico-chemical properties, electrochemistry, purification, inorganic and organic mercury chemistry, industrial application and synthesis and environmental aspects of mercury. This book provides a thorough understanding of amalgam metallurgy which is essential for academics, industrialists and postgraduates working in relevant fields. Guaranteed to bring a wealth of information, this book will be a welcome addition to the literature.

Encyclopedia of Optical Engineering: Pho-Z, pages 2049-3050 Ronald G. Driggers 2003 Compiled by 330 of the most widely respected names in the electro-optical sciences, the Encyclopedia is destined to serve as the premiere guide in the field with nearly 2000 figures, 560 photographs, 260 tables, and 3800 equations. From astronomy to x-ray optics, this reference contains more than 230 vivid entries examining the most intriguing technological advances and perspectives from distinguished professionals around the globe. The contributors have selected topics of utmost importance in areas including digital image enhancement, biological modeling, biomedical spectroscopy, and ocean optics, providing thorough coverage of recent applications in this continually expanding field.

Handbook of Laser Technology and Applications Chunlei Guo 2021-06-24 This comprehensive handbook gives a fully updated guide to lasers and laser systems, including the complete range of their technical applications. The first volume outlines the fundamental components of lasers, their properties and working principles. The second volume gives exhaustive coverage of all major categories of lasers, from solid-state and semiconductor diode to fiber, waveguide, gas, chemical, and dye lasers. The third volume covers modern applications in engineering and technology, including all new and updated case studies spanning telecommunications and data storage to medicine, optical measurement, defense and security, nanomaterials processing and characterization.

Langmuir-Blodgett Films, 1982 G.G. Roberts 2016-10-26 Thin Films Science and Technology, Volume 3: Langmuir-Blodgett Films, 1982 presents the developments and complementary methods for the production of ultrathin films. This book evaluates the process technology and potential of the films. Organized into two parts encompassing 48 chapters, this volume begins with an overview of the idea that the Langmuir-Blodgett method of superimposing fatty acid monolayers might be suitably modified. This text then examines the behavior of anisotropic photoconductivities in Langmuir films of rhodanine containing merocyanines with three donor nuclei diluted with arachidic acid. Other chapters describe the characteristic of pure Langmuir-Blodgett films of porphyrins. This book discusses as well the preliminary resonance Raman spectroscopy experiments on Langmuir-Blodgett films made of a small number of porphyrin layers. The final chapter deals with the need to fabricate small structures in electronic devices because of the advantages of cost and speed. This book is a valuable resource for scientists and engineers.

Device Physics of Narrow Gap Semiconductors Junhao Chu 2009-10-13 Narrow gap semiconductors obey the general rules of semiconductor science, but often exhibit extreme features of these rules because of the same properties that produce their narrow gaps. Consequently these materials provide sensitive tests of theory, and the opportunity for the design of innovative devices. Narrow gap semiconductors are the most important materials for the preparation of advanced modern infrared systems. Device Physics of Narrow Gap Semiconductors, a forthcoming second book, offers descriptions of the materials science and device physics of these unique materials. Topics covered include impurities and defects, recombination mechanisms, surface and interface properties, and the properties of low dimensional systems for infrared applications. This book will help readers to understand not only semiconductor physics and materials science, but also how they relate to advanced opto-electronic devices. The final chapter describes the device physics of photoconductive detectors, photovoltaic infrared detectors, super lattices and quantum wells, infrared lasers, and single photon infrared detectors.

Characterization in Compound Semiconductor Processing Yale Strausser 2010 "Characterization in Compound Semiconductor Processing is for scientists and engineers working with compound semiconductor materials and devices who are not characterization specialists. Materials and processes typically used in R&D and in the fabrication of GaAs, GaAlAs, InP and HgCdTe based devices provide examples of common analytical problems. The book discusses a variety of characterization techniques to provide insight into how each individually, or in combination, might be used in solving problems associated with these materials. The book will help in the selection and application of the appropriate analytical techniques by its coverage of all stages of materials or device processing: substrate preparation, epitaxial growth, dielectric film deposition, contact formation and dopant introduction."--P. [4] of cover.

Perspectives in Optoelectronics

Mercury Cadmium Telluride Peter Capper 2011-06-20 Mercury cadmium telluride (MCT) is the third most well-regarded semiconductor after silicon and gallium arsenide and is the material of choice for use in infrared sensing and imaging. The reason for this is that MCT can be 'tuned' to the desired IR wavelength by varying the cadmium concentration. Mercury Cadmium Telluride: Growth, Properties and Applications provides both an introduction for newcomers, and a comprehensive review of this fascinating material. Part One discusses the history and current status of both bulk and epitaxial growth techniques, Part Two is concerned with the wide range of properties of MCT, and Part Three covers the various device types that have been developed using MCT. Each chapter opens with some historical background and theory before presenting current research. Coverage includes: Bulk growth and properties of MCT and CdZnTe for MCT epitaxial growth Liquid phase epitaxy (LPE) growth Metal-organic vapour phase epitaxy (MOVPE) Molecular beam epitaxy (MBE) Alternative substrates Mechanical, thermal and optical properties of MCT Defects, diffusion, doping and annealing Dry device processing Photoconductive and photovoltaic detectors Avalanche photodiode detectors Room-temperature IR detectors

Noise in Physical Systems and 1/f Fluctuations V Bareikis 1995-04-26 The volume constitutes the proceedings of the 13th International Conference on Noise in Physical Systems and 1/f Fluctuations (ICNF'95) held in Palanga, Lithuania, in the period 29 May – 3 June 1995. International conference of fluctuation phenomena has a rich history. Previous ones were held in St. Louis (USA, 1993), Kyoto (Japan, 1991), Budapest (Hungary, 1989), Montreal (Canada, 1983), etc. The conference proved to be successful in bringing together specialists in fluctuation phenomena in very different areas, and providing a bridge linking theorists and applied scientists involved in the design of new generation of electronic devices.

Correspondingly, the volume covers fundamental aspects of noise in various fields of science and modern technology. Mesoscopic fluctuations, noise in high temperature superconductors, in nanoscale structures, in optoelectronic and microwave devices, fluctuation phenomena in biological systems and human body are in the spotlight. Contents: High-Frequency Noise in Heterostructures (V Bareikis et al.) Noise in Mesoscopic Conductors and Capacitors (M Büttiker) Monte Carlo Simulation of Electron Noise in Nanostructures (V V Mittin et al.) Why is the Noise So Strong in High-Tc Superconductors? (L B Kiss et al.) On the Level-Crossing Problem of Spherically Invariant Random Processes (R Tetzlaff et al.) Plasma and Transit-Time Effects on Electronic Noise in Semiconductor n-n-n Structures (L Reggiani et al.) Contribution of Interparticle Correlations to Electronic Noise in Semiconductors (L Varani) Noise Spectroscopy of Band States in CdS Based Photoconducting Materials (A Carbone & P Mazzetti) Quantum 1/f Noise Theory and Experiment (P H Handel) Flicker Noise and Material Defectness (V Palenskis et al.) Models of Burst and RTS Noise (J Sikula) A New Approach to Calculate Low Frequency Noise Parameters of Electronic Devices (Y-S Dai & X-H Chen) The Gate Voltage Dependence of the 1/f Noise Parameter α in MOS Transistors (L K J Vandamme) Low-Frequency Noise in BJT's and HBT's (T G M Kleinpenning) Correlation between Electrical and Optical 1/f Noises in Laser Diodes as a Function of Series Resistance 1/f Noise (K Daulasim et al.) A Low-Frequency Noise Study of State-of-the-Art Silicon n+p Junction Diodes (E Simoen et al.) Excess Noise and Reliability in Electronic Devices (B K Jones) Phenomenology and Mechanism of 1/f Fluctuations in Neuronal Activities of Cat's Central Nervous System (M Yamamoto) Noisy On-Off Intermittency (A enys & H Lustfeld) Model of the Mechanism of Acoustic Emission in Polycrystalline Ferrites (R Rankis et al.) and other papers Readership: Physicists, electronic engineers and biologists. keywords: *Texas Instruments Technical Journal* 1991-07